

## FDP55N06 / FDPF55N06 N-Channel UniFET<sup>™</sup> MOSFET 60 V, 55 A, 22 mΩ

## Features

- $R_{DS(on)} = 22 \text{ m}\Omega @V_{GS} = 10 \text{ V}, I_D = 27.5 \text{ A}$
- Low Gate Charge (Typ. 30 nC)
- Low Crss (Typ. 60 pF)
- 100% Avalanche Tested



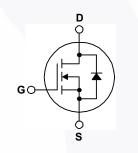
FDP55N06 / FDPF55N06 — N-Channel UniFET<sup>™</sup> MOSFET

## Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted

Symbol	Parameter		FDP55N06	FDPF55N06	Unit
V <sub>DSS</sub>	Drain-Source Voltage		6	50	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^\circ$	C)	55	55 *	А
	- Continuous (T <sub>C</sub> = 100	°C)	34.8	34.8 *	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	220	220 *	А
V <sub>GSS</sub>	Gate-Source Voltage		±	25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	4	80	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	Ę	55	А
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1		1 <sup>.</sup>	1.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4	.5	V/ns
P <sub>D</sub>	Power Dissipation ( $T_c = 25^{\circ}C$ )		114	48	W
	- Derate above 25°C		0.9	0.4	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to	o +150	°C
TL	Maximum lead temperature for soldering purposes,		300		°C
۰L	1/8" from case for 5 seconds				U

\* Drain current limited by maximum junction temperature

## **Thermal Characteristics**

Symbol	Parameter	FDP55N06	FDPF55N06	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	1.1	2.58	°C/W
$R_{ hetaJS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5		°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient, Max,	62.5	62.5	°C/W

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP55N06	FDP55N06	TO-220	Tube	N/A	50 units
FDPF55N06	FDPF55N06	TO-220F	Tube	N/A	50 units

## Electrical Characteristics T<sub>c</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Charac	teristics					1
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ = 0 V, I <sub>D</sub> = 250 µA	60			V
$\Delta BV_{DSS}$ / $\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 µA, Referenced to 25°C		0.05		V/°C
I <sub>DSS</sub> Z	Zero Gate Voltage Drain Current	$V_{DS}$ = 60 V, $V_{GS}$ = 0 V			1	μA
		V <sub>DS</sub> = 48 V, T <sub>C</sub> = 150°C			10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS}$ = -20 V, $V_{DS}$ = 0 V			-100	nA
On Charact	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 27.5 A		0.018	0.022	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 27.5 A		33		S
Dynamic Cl	haracteristics				I	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 V, V_{GS} = 0 V,$		1160	1510	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		375	490	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			60	90	pF
Switching C	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 55 A,		30	65	ns
t <sub>r</sub>	Turn-On Rise Time	- R <sub>G</sub> = 25 Ω		130	265	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	70	150	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		95	195	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 55A,		30	37	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		6.5		nC
Q <sub>qd</sub>	Gate-Drain Charge	(Note 4)		7.5		nC
0	Leven Diode Characteristics and Maximum Ratings	5				<u> </u>
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Fo				55	А
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				220	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 55 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 V, I_S = 55 A,$		40		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_{\rm F} / dt = 100  {\rm A}/{\rm \mu s}$		55		μC

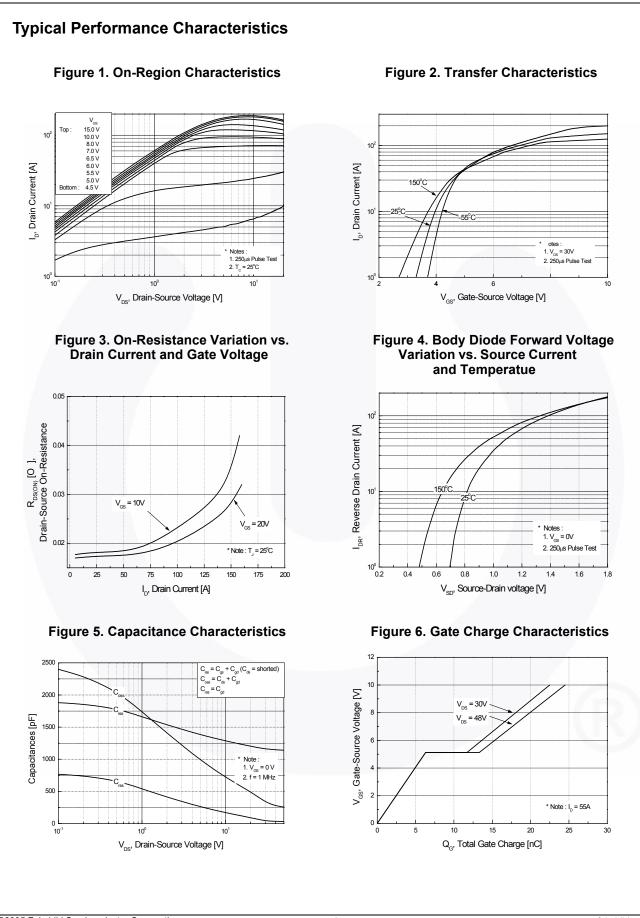
Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature

2. L = 5.6mH, I\_{AS} = 55A, V\_DD = 50V, R\_G = 25  $\Omega,$  Starting  $\mbox{ T}_{J}$  = 25°C

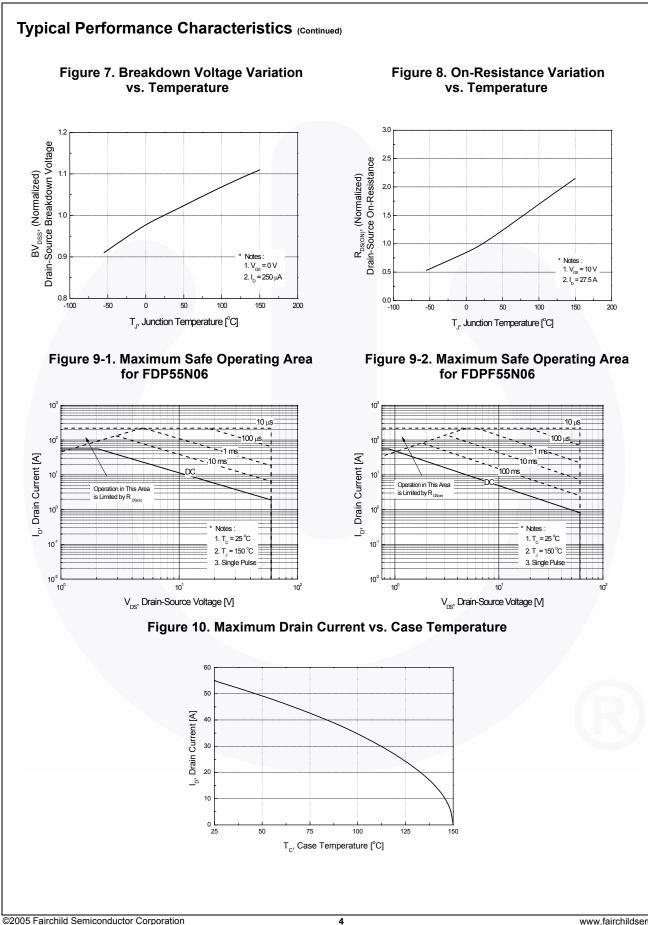
3. I\_{SD} \leq 55A, di/dt  $\leq$  200A/µs, V\_{DD}  $\leq$  BV\_{DSS,} Starting ~T\_J = 25°C

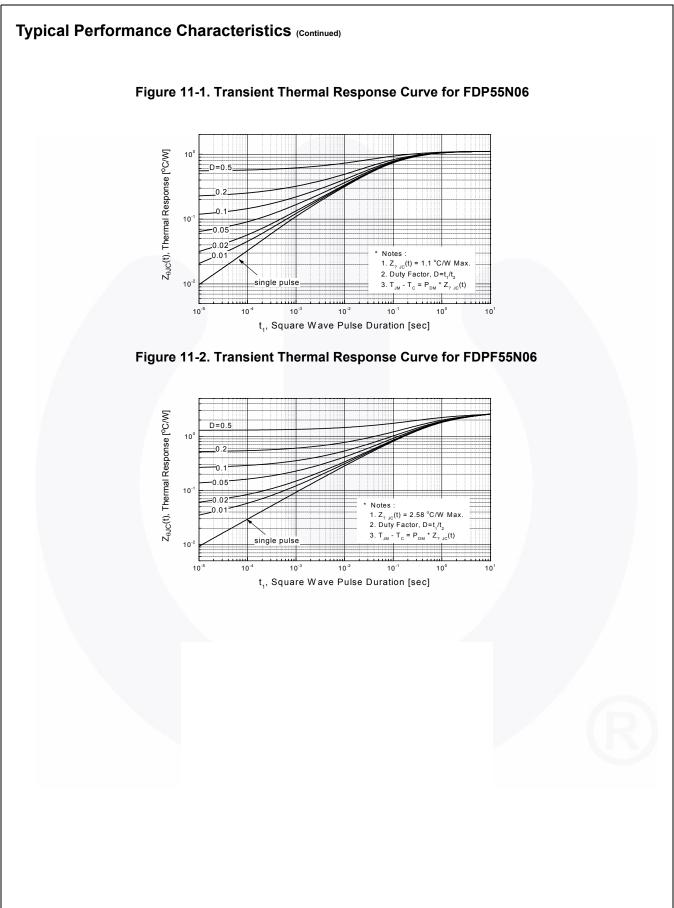
4. Essentially independent of operating temperature



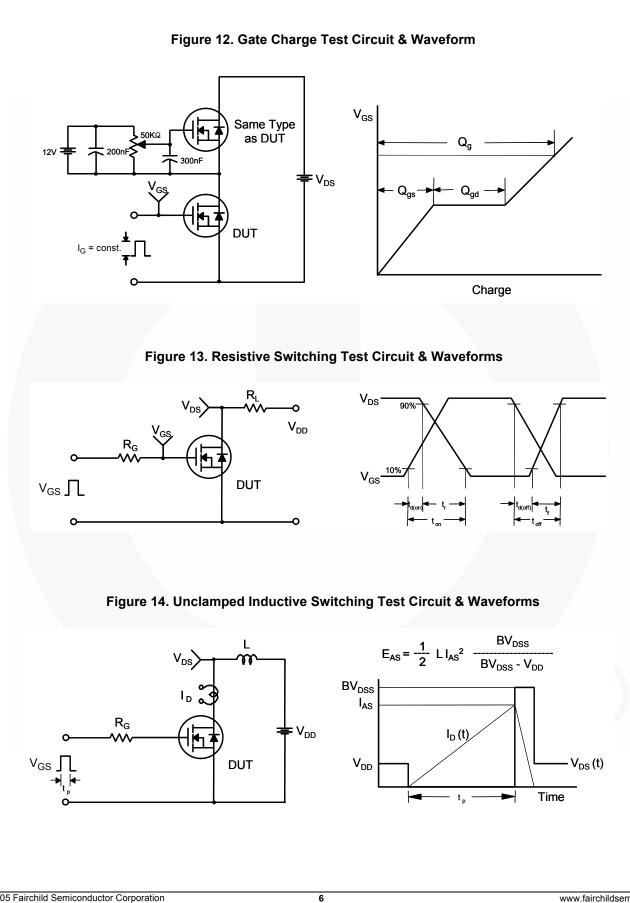
©2005 Fairchild Semiconductor Corporation FDP55N06 / FDPF55N06 Rev. C0

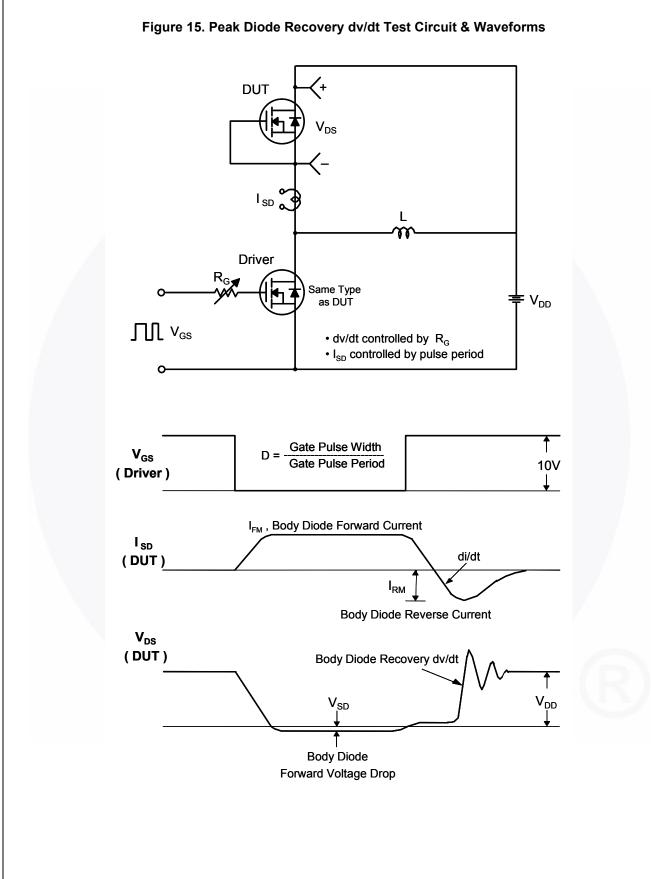
FDP55N06 / FDPF55N06 — N-Channel UniFET<sup>™</sup> MOSFET

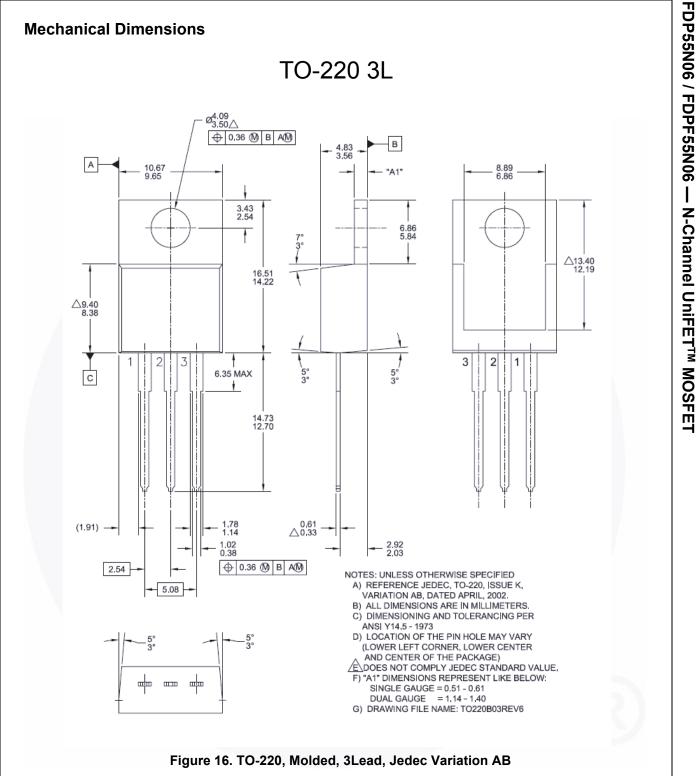




5





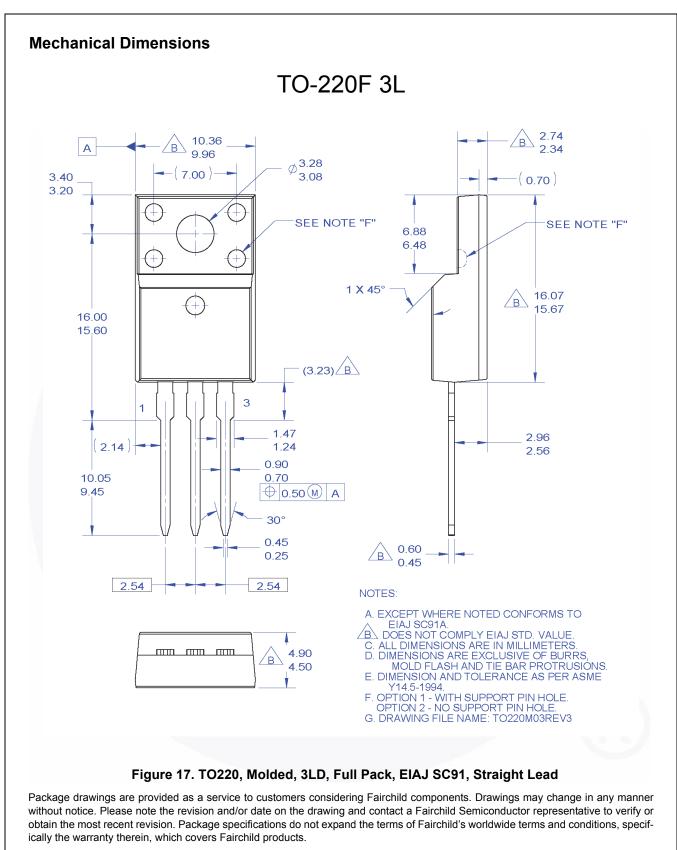


Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT220-003

**Dimension in Millimeters** 



Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TF220-003

**Dimension in Millimeters** 



SEMICONDUCTOR

### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

	an odorr a ddorriarito.	
AccuPower™	F-PFS™	-215
AX-CAP <sup>®</sup> *	FRFET <sup>®</sup>	
BitSiC™	Global Power Resource <sup>SM</sup>	PowerTrench <sup>®</sup>
Build it Now™	GreenBridge™	PowerXS™
CorePLUS™	Green FPS™	Programmable Active Droop™
CorePOWER™	Green FPS™ e-Series™	QFĔT <sup>®</sup>
CROSSVOLT™	Gmax™	QS™
CTL™	GTO™	Quiet Series™
Current Transfer Logic™	IntelliMAX™	RapidConfigure™
DEUXPEED®	ISOPLANAR™	
Dual Cool™	Marking Small Speakers Sound Louder	
EcoSPARK <sup>®</sup>	and Better™	Saving our world, 1mW/W/kW at a time™
EfficentMax™	MegaBuck™	SignalWise™
ESBC™	MICROCOUPLER™	SmartMax™
<b>e</b>	MicroFET™	SMART START™
<i>t</i>	MicroPak™	Solutions for Your Success™
Fairchild®	MicroPak2™	SPM®
Fairchild Semiconductor <sup>®</sup>	MillerDrive™	STEALTH™
FACT Quiet Series™	MotionMax <sup>™</sup>	SuperFET <sup>®</sup>
FACT®	mWSaver®	SuperSOT™-3
FAST®	OptoHiT™ OPTOLOCI0®	SuperSOT™-6
FastvCore™	OPTOLOGIC <sup>®</sup> OPTOPLANAR <sup>®</sup>	SuperSOT™-8 SupreMOS <sup>®</sup>
FETBench™	UPTOPLANAR*	
FPS™		SyncFET™

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Sync-Lock™ SYSTEM<sup>®\*</sup> GENERAL

TinyBoost TinyBuck® TinyCalc™ TinyLogic® TINYOPTO™

TinvPower™ TinyPWM™

TinyWire™

TranSiC™

UHC® Ultra FRFET™

VCX™

XS™

UniFFT™

VisualMax™

VoltagePlus™

TriFault Detect™

TRUECURRENT®\* µSerDes™

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

FDP55N06 / FDPF55N06 — N-Channel UniFET<sup>TM</sup> MOSFET

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor: <u>FDPF55N06</u>